Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	11786	((438/382) or (257/E21.004) or (257/E21.415) or (257/E21.616) or (257/E21.703) or (257/E27.016) or (257/E27.112) or (257/E29.147) or (257/E29.151) or (438/330) or (438/583) or (438/649)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/11 13:50
L5	899	4 and resistor and (silicide salicide salicade)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 13:51
L6	9	(("6399451") or ("20030025135") or ("20020079544") or ("6136636") or ("20030057439") or ("20030025135") or ("5710450") or ("6121200") or ("6432754") or ("6049114")).PN.	US-PGPUB; USPAT; JPO	OR	OFF	2007/01/11 13:52
S19	2	(("20040065927") or ("6703648")). PN.	US-PGPUB; USPAT; JPO	OR	OFF	2007/01/10 16:07
S20	7	("6703648") URPN.	USPAT	OR	ON	2005/12/30 12:40
S21	9	("5891769" "6225176" "6274894" "6303451" "6326664" "6361874" "6506653" "6518155" "6524920").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/30 12:44
S24	1397	(257/288) CCLS.	US-PGPUB; USPAT; JPO	OR	OFF	2006/01/03 14:37
S25	219	S24 and ((silicon near on near insulat\$3) SOI)	US-PGPUB; USPAT; JPO	OR	ON	2006/01/03 14:38
S26	44106	chen.in.	US-PGPUB; USPAT; JPO	OR	ON	2006/01/03 16:34
S27	17792	wu.in.	US-PGPUB; USPAT; JPO	OR	ON	2006/01/03 16:11
S28	406	S26 and soi	US-PGPUB; USPAT; JPO	OR	ON	2006/01/03 16:36
S29	157	S27 and soi	US-PGPUB; USPAT; JPO	OR	ON	.2006/01/03 16:11
S30	0	("6784101").URPN.	USPAT	OR	ON	2006/01/03 16:27
S31		("20020100942" "20030049942" "4181538" "6063698" "6100204" "6197641" "6444592" "6509587"). PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/01/03 16:27

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S32	26248	S26 and @pd<"20030929"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/03 16:35
S34	10691	S27 and @pd<"20030929"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/03 16:36
S35	160	S32 and soi	US-PGPUB; USPAT; JPO	OR	ON	2006/01/03 16:43
S36	66	S34 and soi	US-PGPUB; USPAT; JPO	OR .	ON	2006/01/03 16:36
\$37	5	"6521949"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/03 16:43
S38	. 9	("5486282" "5534094" "5776823" "5796166" "6271541").PN. OR ("6521949").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/01/03 17:16
S39	5	("20010009792" "5863824" "5877530" "6433871" "6703648"). PN. OR ("6838777").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/01/03 17:27

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S40	94	("20010001724" "20010009303" "20010031535" "20010045604" "20020019127" "20020048910" "20020052084" "20020056879" "20020063292" "20020190284" "20030113971" "20040007724" "20040014276" "20040014304" "20040070035" "20040084735" "20040119101" "20040142545" "20040173815" "4717681" "4755478" "4803539" "5034348" "5089872" "5198689" "5217923" "5242847" "5334861" "5336903" "5346840" "5442205" "5496750" "5496771" "5659194" "5714777" "5844260" "5847419" "5869359" "5877535" "5891769" "5933741" "5998807" "6008111" "6066563" "6132806" "6133124" "6159856" "6187657" "6214679" "6235575" "6246077" "6251780" "6268257" "6281532" "6291321" "6294448" "6306698" "6313486" "6315384" "6316357" "6319805" "6362071" "6380008" "6399970" "6406986" "6410371" "6461960" "6486520" "6498359" "6555880" "6562703" "6555839" "6555880" "6562703" "6593641" "6693156" "6695498" "6621131" "6667223" "6682965" "6686617" "6699765" "6703648" "6724019" "6743684").PN. OR	US-PGPUB; USPAT; USOCR	OR	ON	2006/01/04 09:42
S56	35	("6946371").URPN. "6136636"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/05 14:00
S57	7035	polycide	US-PGPUB; USPAT; JPO	OR	ON	2006/01/05 14:04
S61	34	(shallow near region) and (strain\$3 near2 channel)	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 08:29
S62	22416	Noda.in.	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 08:29
S63	142	S62 and fet	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 08:31
S64	11	S62 and sige	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 08:29

S65	4	(("5268324") or ("5583059") or ("6358806") or ("20040175872")). PN.	US-PGPUB; USPAT; JPO	OR	OFF	2006/01/06 11:04
S66	0	("US20050051851A1").PN.	US-PGPUB; USPAT; JPO	OR	OFF	2006/01/06 11:04
S67	1	("2005005185").PN.	US-PGPUB; USPAT; JPO	OR .	OFF	2006/01/06 11:17
S68	3	10/605134	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 11:06
S69	4	("20040175872" "5268324" "5583059" "6358806").PN. OR ("6906360").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/01/06 11:07
S70	1	("20050098854").PN.	US-PGPUB; USPAT; JPO	OR	OFF	2006/01/06 11:17
S71	2	10/192657	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 11:25
S72	6	("5591650" "6004853" "6049114" "6121100" "6249026" "6399451").PN. OR ("6806537"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/01/06 11:26
S73	134986	FET "field effect transistor"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 14:25
S74	8966	S73 and (source drain 's/d' source/drain) near3 (under below beneath underneath subordinate buried)	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 14:28
S75	8966	S73 and ((source drain 's/d' source/drain) near3 (under below beneath underneath subordinate buried))	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 14:28
S76	6429	S75 and (metal (silicon near germanium) (metal near alloy))	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 14:31
S77	2113	S76 and (silicide salicide)	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 14:33
S78	2106	S77 and ((stack gate) or gate)	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 14:33
S79	316	S78 and (second near3 (spacer (side near2 spacer)))	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 14:34
S80	215	S79 and @pd<"20030929"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 15:09

S81	34	S80 and (silicon near3 germanium)	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 15:28
S82	1422	S78 and @pd<"20030929"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 15:09
S83	4852072	"14" not S79	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 15:09
S84	4134551	"15" not S79	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 15:09
S85	1207	S82 not S79	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 15:10
S86	7106	(257/66,72,347,192,616).CCLS.	US-PGPUB; USPAT; JPO	OR	OFF	2006/01/18 16:01
S87	1114	S86 and (silicon near germanium)	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 15:30
S88	510	S86 and (silicon near germanium) and (silicide salicide)	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 15:30
S89	225	S86 and (silicon near germanium) and (silicide salicide) and @pd<"20030929"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/08 11:56
S90	4859	S86 and @pd<"20030929"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/06 15:30
S91	4	"6432754"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/08 12:01
S92	1	"20020190284"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/08 12:01
S93	10	"6399451"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/08 13:35
S94	10	(("6399451") or ("20030025135") or ("20020079544") or ("6136636") or ("20030057439") or ("20030025135") or ("5710450") or ("6121200") or ("6521949") or ("6432754") or ("6049114")).PN.	US-PGPUB; USPAT	OR	OFF	2006/01/09 09:54
S95	10	(("6399451") or ("20030025135") or ("20020079544") or ("6136636") or ("20030057439") or ("20030025135") or ("5710450") or ("6121200") or ("6521949") or ("6432754") or ("6049114")).PN.	US-PGPUB; USPAT; JPO	OR	OFF	2006/01/09 09:55

S96	11	(("6399451") or ("20030025135") or ("20020079544") or ("6136636") or ("20030057439") or ("20020190284") or ("5710450") or ("6121200") or ("6521949") or ("6432754") or ("6049114")).PN.	US-PGPUB; USPAT; JPO	OR	OFF	2006/01/09 09:58
S97	1	("6121100").PN.	US-PGPUB; USPAT; JPO	OR	OFF	2006/01/09 10:45
S98	7126	(257/66,72,347,192,616).CCLS.	US-PGPUB; USPAT; JPO	OR	OFF	2006/01/18 16:01
S99	216	S98 and resistor and silicide	US-PGPUB; USPAT; JPO	OR	ON	2006/01/18 17:06
S10 0	4	"6555637"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/18 16:23
S10 1	3	"6555865"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/18 16:24
S10 2	1	"6586311"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/18 16:47
S10 3	5	("5352923" "5656524" "5930638" "6350652" "6365481").PN. OR ("6586311").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/01/18 16:47
S10 4	5	("5352923" "5656524" "5930638" "6350652" "6365481").PN. OR ("6586311").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/01/18 16:53
S10 5	96	S99 and ('Tantalum nitride' 'TaN' 'TiN' 'Titanium Nitride' 'Nickel Chromium' 'NiCr' 'SiCr' 'silicon chromium')	US-PGPUB; USPAT; JPO	OR	ON	2006/01/18 17:17
S10 6	96	S99 and ('Tantalum nitride' 'TaN' 'TiN' 'Titanium Nitride' 'Nickel Chromium' 'NiCr' 'SiCr' 'silicon chromium') and resist\$3	US-PGPUB; USPAT; JPO	OR	ON	2006/01/18 17:17
S10 7	96	S99 and ('Tantalum nitride' 'TaN' 'TiN' 'Titanium Nitride' 'Nickel Chromium' 'NiCr' 'SiCr' 'silicon chromium') and resistor	US-PGPUB; USPAT; JPO	OR	ON	2006/01/18 17:18
S10 8	94	S99 and ('Tantalum nitride' 'TaN' 'TiN' 'Titanium Nitride' 'Nickel Chromium' 'NiCr' 'SiCr' 'silicon chromium') and resistor and transistor	US-PGPUB; USPAT; JPO	OR	ON	2006/01/18 17:18
S10 9	94	S99 and ('Tantalum nitride' 'TaN' 'TiN' 'Titanium Nitride' 'Nickel Chromium' 'NiCr' 'SiCr' 'silicon chromium') and resistor and transistor and silicide	US-PGPUB; USPAT; JPO	OR	ON	2006/01/18 17:18

S11 0	94	S99 and ('Tantalum nitride' 'TaN' 'TiN' 'Titanium Nitride' 'Nickel Chromium' 'NiCr' 'SiCr' 'silicon chromium') and resistor and transistor and (silicide salicide)	US-PGPUB; USPAT; JPO	OR	ON	2006/01/19 13:27
S11 1	4	"6670637"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/18 17:23
S11 2	7140	(257/66,72,347,192,616).CCLS.	US-PGPUB; USPAT <u>;</u> JPO	OR	OFF	2006/01/19 13:27
S11 3	216	S112 and resistor and silicide	US-PGPUB; USPAT; JPO	OR	ON	2006/01/19 13:27
S11 4	96	S113 and ('Tantalum nitride' 'TaN' 'TiN' 'Titanium Nitride' 'Nickel Chromium' 'NiCr' 'SiCr' 'silicon chromium') and resistor and (silicide salicide)	US-PGPUB; USPAT; JPO	OR	ON	2006/01/19 13:32
S11 5	94	S113 and ('Tantalum nitride' 'TaN' 'TiN' 'Titanium Nitride' 'Nickel Chromium' 'NiCr' 'SiCr' 'silicon chromium') and resistor and transistor and (silicide salicide)	US-PGPUB; USPAT; JPO	OR	ON	2006/01/19 13:28
S11 6	2	S114 not S115	US-PGPUB; USPAT; JPO	OR	ON	2006/01/19 13:31
S11 7	668	resistor and ('Tantalum nitride' 'TaN' 'TiN' 'Titanium Nitride' 'Nickel Chromium' 'NiCr' 'SiCr' 'silicon chromium') and (STI trench near isolation)	US-PGPUB; USPAT; JPO	OR	ON	2006/01/19 13:32
S11 8	605	resistor and ('Tantalum nitride' 'TaN' 'TiN' 'Titanium Nitride' 'Nickel Chromium' 'NiCr' 'SiCr' 'silicon chromium') and (STI trench near isolation) and transistor	US-PGPUB; USPAT; JPO	OR	ON	2006/01/19 13:32 ,
S11 9	430	resistor and ('Tantalum nitride' 'TaN' 'TiN' 'Titanium Nitride' 'Nickel Chromium' 'NiCr' 'SiCr' 'silicon chromium') and (STI trench near isolation) and transistor and (silicide salicide)	US-PGPUB; USPAT; JPO	OR	ON	2006/01/19 13:33
S12 0	233	resistor and ('Tantalum nitride' 'TaN' 'TiN' 'Titanium Nitride' 'Nickel Chromium' 'NiCr' 'SiCr' 'silicon chromium') and (STI trench near isolation) and transistor and (silicide salicide) and spacer	US-PGPUB; USPAT; JPO	OR	ON	2006/01/19 13:35
S12 1	138	S120 and @pd<"20040806"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/19 13:41

S12 2	3	"6777752"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/19 13:41
S12 3	4	("4559694" "5554873").PN. OR ("6777752").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/01/19 14:22
S12 4	37	("4208781" "4209716" "4370798" "4377819" "4391650" "4416049" "4419812" "4467519" "4577390" "4579600" "4679170" "5187559" "5196233" "5198382" "5218225" "5273924" "5313087" "5352923" "5365099" "5448103").PN. OR ("5554873").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/01/19 14:30
S12 5	4	(("6184143") or ("6403459") or ("6645821") or ("20010049199")). PN.	US-PGPUB; USPAT; JPO	OR	OFF	2006/01/20 08:57
S12 6	0	(("10605134") or ("10604607")).PN.	US-PGPUB; USPAT; JPO	OR	OFF	2006/01/20 08:57
S12 7	2	(("0605134") or ("0604607")).PN.	US-PGPUB; USPAT; JPO	OR	OFF	2006/01/20 08:57
S12 8	6	10/605,134 10/604,607	US-PGPUB; USPAT; JPO	OR	ON	2006/01/20 08:58
S12 9	1	"6946371"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/20 10:14
S13 0	30	"6049114"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/20 10:16
S13 1	30	"6121100"	US-PGPUB; USPAT; JPO	OR	ON	2006/01/20 10:16
S13 2	. 1	("20060065914").PN.	US-PGPUB; USPAT; JPO	OR	OFF	2006/07/10 10:11
S13 3	0	(FET and substrate and sidewalls and gate and (semiconductor near alloy) and drain and source and distance and (silicon adj gemanium)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 10:59
S13 4	0	(FET and substrate and sidewalls and gate and drain and source and distance and (silicon adj gemanium)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 11:00

S13 5	1	(FET and substrate and sidewalls and gate and drain and source and distance and (silicon adj germanium)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/10 11:00
S13 6	794	resistor and ('Tantalum nitride' 'TaN' 'TiN' 'Titanium Nitride' 'Nickel Chromium' 'NiCr' 'SiCr' 'silicon chromium') and (STI trench near isolation) and transistor and (silicide salicide) and spacer	US-PGPUB; USPAT; JPO	OR	ON	2006/07/10 11:18
S13 7	451	S136 and @pd<"20040806"	US-PGPUB; USPAT; JPO	OR	ON	2006/07/10 11:18
S13 8	1489	(257/288) CCLS.	US-PGPUB; USPAT; JPO	OR	OFF	2006/07/10 11:18
S13 9	7600	(257/66,72,347,192,616).CCLS.	US-PGPUB; USPAT; JPO	OR	OFF	2006/07/10 11:19
S14 0	1504	(257/288).CCLS.	US-PGPUB; USPAT; JPO	OR	OFF	2006/07/23 19:31
S14 1	142455	FET "field effect transistor"	US-PGPUB; USPAT; JPO	OR T	ON	2006/07/23 19:31
S14 2	9559	S141 and ((source drain 's/d' source/drain) near3 (under below beneath underneath subordinate buried))	US-PGPUB; USPAT; JPO	OR	ON	2006/07/23 19:31
S14 3	6915	S142 and (metal (silicon near germanium) (metal near alloy))	US-PGPUB; USPAT; JPO	OR	ON	2006/07/23 19:31
S14 4	7652	(257/66,72,347,192,616).CCLS.	US-PGPUB; USPAT; JPO	OR	OFF	2006/07/23 19:31
S14 5	232	S144 and resistor and silicide	US-PGPUB; USPAT; JPO	OR	ON	2006/07/23 19:31
S14 6	227	S145 and ('Tantalum nitride' 'TaN' 'TiN' 'Titanium Nitride' 'Nickel Chromium' 'NiCr' 'SiCr' 'silicon chromium') and resistor and transistor and (silicide salicide)	US-PGPUB; USPAT; JPO	OR	ON	2006/07/23 19:31
S14 7	7652	(257/66,72,347,192,616).CCLS.	US-PGPUB; USPAT; JPO	OR	OFF	2006/07/23 19:31

S14 8	798	resistor and ('Tantalum nitride' 'TaN' 'TiN' 'Titanium Nitride' 'Nickel Chromium' 'NiCr' 'SiCr' 'silicon chromium') and (STI trench near isolation) and transistor and (silicide salicide) and spacer	US-PGPUB; USPAT; JPO	OR	ON	2006/07/23 19:31
S14 9	451	S148 and @pd<"20040806"	US-PGPUB; USPAT; JPO	OR	ON	2006/07/23 19:31
S15 0	2	"20060027878"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2007/01/10 16:07

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